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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details

Product Status	Active
Architecture	MCU, FPGA
Core Processor	Dual ARM® Cortex®-A53 MPCore™ with CoreSight™, Dual ARM®Cortex™-R5 with CoreSight™
Flash Size	-
RAM Size	256KB
Peripherals	DMA, WDT
Connectivity	CANbus, EBI/EMI, Ethernet, I ² C, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Speed	500MHz, 1.2GHz
Primary Attributes	Zynq®UltraScale+™ FPGA, 154K+ Logic Cells
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	625-BFBGA, FCBGA
Supplier Device Package	625-FCBGA (21x21)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xczu3cg-l1sfva625i

Table 1: Absolute Maximum Ratings⁽¹⁾ (Cont'd)

Symbol	Description	Min	Max	Units
V _{CCO_PSDDR}	PS DDR I/O supply voltage.	-0.500	1.650	V
V _{CC_PSDDR_PLL}	PS DDR PLL supply voltage.	-0.500	2.000	V
V _{CCO_PSIO}	PS I/O supply.	-0.500	3.630	V
V _{PSIN} ⁽²⁾	PS I/O input voltage.	-0.500	V _{CCO_PSIO} + 0.550	V
	PS DDR I/O input voltage.	-0.500	V _{CCO_PSDDR} + 0.550	V
V _{CC_PSBATT}	PS battery-backed RAM and battery-backed real-time clock (RTC) supply voltage.	-0.500	2.000	V
Programmable Logic (PL)				
V _{CCINT}	Internal supply voltage.	-0.500	1.000	V
V _{CCINT_IO} ⁽³⁾	Internal supply voltage for the I/O banks.	-0.500	1.000	V
V _{CCAUX}	Auxiliary supply voltage.	-0.500	2.000	V
V _{CCBRAM}	Supply voltage for the block RAM memories.	-0.500	1.000	V
V _{CCO}	Output drivers supply voltage for HD I/O banks.	-0.500	3.400	V
	Output drivers supply voltage for HP I/O banks.	-0.500	2.000	V
V _{CCAUX_IO} ⁽⁴⁾	Auxiliary supply voltage for the I/O banks.	-0.500	2.000	V
V _{REF}	Input reference voltage.	-0.500	2.000	V
V _{IN} ⁽²⁾⁽⁵⁾⁽⁷⁾	I/O input voltage for HD I/O banks. ⁽⁶⁾	-0.550	V _{CCO} + 0.550	V
	I/O input voltage for HP I/O banks.	-0.550	V _{CCO} + 0.550	V
I _{DC}	Available output current at the pad.	-20	20	mA
I _{RMS}	Available RMS output current at the pad.	-20	20	mA
GTH or GTY Transceiver				
V _{MGTAVCC}	Analog supply voltage for transceiver circuits.	-0.500	1.000	V
V _{MGTAVTT}	Analog supply voltage for transceiver termination circuits.	-0.500	1.300	V
V _{MGTVCCAUX}	Auxiliary analog Quad PLL (QPLL) voltage supply for transceivers.	-0.500	1.900	V
V _{MGTREFCLK}	Transceiver reference clock absolute input voltage.	-0.500	1.300	V
V _{MGTAVTTRCAL}	Analog supply voltage for the resistor calibration circuit of the transceiver column.	-0.500	1.300	V
V _{IN}	Receiver (RXP/RXN) and transmitter (TXP/TXN) absolute input voltage.	-0.500	1.200	V
I _{DCIN-FLOAT}	DC input current for receiver input pins DC coupled RX termination = floating. ⁽⁸⁾	-	10	mA
I _{DCIN-MGTAVTT}	DC input current for receiver input pins DC coupled RX termination = V _{MGTAVTT} .	-	10	mA
I _{DCIN-GND}	DC input current for receiver input pins DC coupled RX termination = GND. ⁽⁹⁾	-	0	mA
I _{DCIN-PROG}	DC input current for receiver input pins DC coupled RX termination = programmable. ⁽¹⁰⁾	-	0	mA
I _{DCOUT-FLOAT}	DC output current for transmitter pins DC coupled RX termination = floating.	-	6	mA
I _{DCOUT-MGTAVTT}	DC output current for transmitter pins DC coupled RX termination = V _{MGTAVTT} .	-	6	mA

Recommended Operating Conditions

 Table 2: Recommended Operating Conditions⁽¹⁾⁽²⁾

Symbol	Description	Min	Typ	Max	Units
Processor System					
V _{CC_PSINTFP} ⁽³⁾	PS full-power domain supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V _{CCINT} = 0.72V) devices: PS full-power domain supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS full-power domain supply voltage.	0.873	0.900	0.927	V
V _{CC_PSINTLP}	PS low-power domain supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V _{CCINT} = 0.72V) devices: PS low-power domain supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS low-power domain supply voltage.	0.873	0.900	0.927	V
V _{CC_PSAUX}	PS auxiliary supply voltage.	1.710	1.800	1.890	V
V _{CC_PSINTFP_DDR} ⁽³⁾	PS DDR controller and PHY supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V _{CCINT} = 0.72V) devices: PS DDR controller and PHY supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS DDR controller and PHY supply voltage.	0.873	0.900	0.927	V
V _{CC_PSADC}	PS SYSMON ADC supply voltage relative to GND_PSADC.	1.710	1.800	1.890	V
V _{CC_PSPLL}	PS PLL supply voltage.	1.164	1.200	1.236	V
V _{PS_MGTRAVCC}	PS-GTR supply voltage.	0.825	0.850	0.875	V
V _{PS_MGTRAVTT}	PS-GTR termination voltage.	1.746	1.800	1.854	V
V _{CCO_PSDDR} ⁽⁴⁾	PS DDR I/O supply voltage.	1.06	–	1.575	V
V _{CC_PSDDR_PLL}	PS DDR PLL supply voltage.	1.710	1.800	1.890	V
V _{CCO_PSIO} ⁽⁵⁾	PS I/O supply.	1.710	–	3.465	V
V _{PSIN}	PS I/O input voltage.	–0.200	–	V _{CCO_PSIO} + 0.200	V
	PS DDR I/O input voltage.	–0.200	–	V _{CCO_PSDDR} + 0.200	
V _{CC_PSBATT} ⁽⁶⁾	PS battery-backed RAM and battery-backed real-time clock (RTC) supply voltage.	1.200	–	1.500	V
Programmable Logic					
V _{CCINT}	PL internal supply voltage.	0.825	0.850	0.876	V
	For -1LI and -2LE (V _{CCINT} = 0.72V) devices: PL internal supply voltage.	0.698	0.720	0.742	V
	For -3E devices: PL internal supply voltage.	0.873	0.900	0.927	V
V _{CCINT_IO} ⁽⁷⁾	PL internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -1LI and -2LE (V _{CCINT} = 0.72V) devices: PL internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -3E devices: PL internal supply voltage for the I/O banks.	0.873	0.900	0.927	V
V _{CCBRAM}	Block RAM supply voltage.	0.825	0.850	0.876	V
	For -3E devices: block RAM supply voltage.	0.873	0.900	0.927	V
V _{CCAUX}	Auxiliary supply voltage.	1.746	1.800	1.854	V

Table 4: DC Characteristics Over Recommended Operating Conditions (Cont'd)

Symbol	Description	Min	Typ ⁽¹⁾	Max	Units
Differential termination	Programmable differential termination (TERM_100) for HP I/O banks.	-35%	100	+35%	Ω
n	Temperature diode ideality factor.	-	1.026	-	-
r	Temperature diode series resistance.	-	2	-	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. For HP I/O banks with a V_{CC0} of 1.8V and separated V_{CC0} and $V_{CCAUX_{IO}}$ power supplies, the I_L maximum current is 70 μ A.
3. This measurement represents the die capacitance at the pad, not including the package.
4. Maximum value specified for worst case process at 25°C.
5. I_{CC_PSBATT} is measured when the battery-backed RAM (BBRAM) is enabled.
6. Do not program eFUSE during device configuration (e.g., during configuration, during configuration readback, or when readback CRC is active).
7. If VRP resides at a different bank (DCI cascade), the range increases to $\pm 15\%$.
8. VRP resistor tolerance is (240 Ω $\pm 1\%$)
9. On-die input termination resistance, for more information see the *UltraScale Architecture SelectIO Resources User Guide (UG571)*.

Table 5: PS MIO Pull-up and Pull-down Current

Symbol	Description	Min	Max	Units
I_{RPU}	Pad pull-up (when selected) at $V_{IN} = 0V$, $V_{CC0_PSMIO} = 3.3V$.	20	80	μ A
	Pad pull-up (when selected) at $V_{IN} = 0V$, $V_{CC0_PSMIO} = 2.5V$.	20	80	μ A
	Pad pull-up (when selected) at $V_{IN} = 0V$, $V_{CC0_PSMIO} = 1.8V$.	15	65	μ A
I_{RPD}	Pad pull-down (when selected) at $V_{IN} = 3.3V$.	20	80	μ A
	Pad pull-down (when selected) at $V_{IN} = 2.5V$.	20	80	μ A
	Pad pull-down (when selected) at $V_{IN} = 1.8V$.	15	65	μ A

Quiescent Supply Current

Table 9: Typical Quiescent Supply Current⁽¹⁾⁽²⁾⁽³⁾⁽⁴⁾

Symbol	Description	Device	Speed Grade and V _{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
I _{CCINTQ}	Quiescent V _{CCINT} supply current.	XCZU2	N/A	393	393	344	344	mA
		XCZU3	N/A	393	393	344	344	mA
		XCZU4	719	684	684	601	601	mA
		XCZU5	719	684	684	601	601	mA
		XCZU6	1629	1549	1549	1358	1358	mA
		XCZU7	1263	1201	1201	1055	1055	mA
		XCZU9	1629	1549	1549	1358	1358	mA
		XCZU11	1786	1699	1699	1491	1491	mA
		XCZU15	1987	1890	1890	1660	1660	mA
		XCZU17	2728	2594	2594	2275	2275	mA
		XCZU19	2728	2594	2594	2275	2275	mA
I _{CCINT_IOQ}	Quiescent V _{CCINT_IO} supply current.	XCZU2	N/A	44	44	44	44	mA
		XCZU3	N/A	44	44	44	44	mA
		XCZU4	61	59	59	59	59	mA
		XCZU5	61	59	59	59	59	mA
		XCZU6	61	59	59	59	59	mA
		XCZU7	120	115	115	115	115	mA
		XCZU9	61	59	59	59	59	mA
		XCZU11	120	115	115	115	115	mA
		XCZU15	61	59	59	59	59	mA
		XCZU17	164	158	158	158	158	mA
		XCZU19	164	158	158	158	158	mA
I _{CCOQ}	Quiescent V _{CCO} supply current.	All devices	1	1	1	1	1	mA
I _{CCAUXQ}	Quiescent V _{CCAUX} supply current.	XCZU2	N/A	55	55	55	55	mA
		XCZU3	N/A	55	55	55	55	mA
		XCZU4	90	90	90	90	90	mA
		XCZU5	90	90	90	90	90	mA
		XCZU6	227	227	227	227	227	mA
		XCZU7	174	174	174	174	174	mA
		XCZU9	227	227	227	227	227	mA
		XCZU11	255	255	255	255	255	mA
		XCZU15	266	266	266	266	266	mA
		XCZU17	396	396	396	396	396	mA
		XCZU19	396	396	396	396	396	mA

PS-PL Power Sequencing

The PS and PL power supplies are fully independent. All PS power supplies can be powered before or after any PL power supplies. The PS and PL power regions are isolated to prevent damage.

Power Supply Requirements

Table 10 shows the minimum current, in addition to I_{CCQ} maximum, required by each Zynq UltraScale+ device for proper power-on and configuration. If the current minimums shown in Table 10 are met, the device powers on after all supplies have passed through their power-on reset threshold voltages. The device must not be configured until after V_{CCINT} is applied. Once initialized and configured, use the Xilinx Power Estimator (XPE) tools to estimate current drain on these supplies.

Table 10: Power-on Current by Device⁽¹⁾

I_{CC} Min =	I_{CCQ} +	XCZU2	XCZU3	XCZU4	XCZU5	XCZU6	XCZU7	XCZU9	XCZU11	XCZU15	XCZU17	XCZU19	Units
$I_{CCINTMIN}$	I_{CCINTQ}^+	464	464	770	770	1800	1514	1800	1961	2242	3433	3433	mA
$I_{CCINT_IOMIN}^+$ $I_{CCBRAMMIN}$	$I_{CCBRAMQ}^+$ $I_{CCINT_IOQ}^+$	155	155	257	257	600	505	600	654	748	1145	1145	mA
I_{CCOMIN}	I_{CCOQ}^+	50	50	50	50	50	50	50	55	63	96	96	mA
$I_{CCAUXMIN}^+$ I_{CCAUX_IOMIN}	I_{CCAUXQ}^+ $I_{CCAUX_IOQ}^+$	111	111	386	386	650	362	650	709	810	1240	1240	mA

Notes:

1. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at www.xilinx.com/power) to estimate power-on current for all supplies.

Table 11 shows the power supply ramp time.

Table 11: Power Supply Ramp Time

Symbol	Description	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 95% of V_{CCINT} .	0.2	40	ms
T_{VCCINT_IO}	Ramp time from GND to 95% of V_{CCINT_IO} .	0.2	40	ms
T_{VCCINT_VCU}	Ramp time from GND to 95% of V_{CCINT_VCU} .	0.2	40	ms
T_{VCCO}	Ramp time from GND to 95% of V_{CCO} .	0.2	40	ms
T_{VCCAUX}	Ramp time from GND to 95% of V_{CCAUX} .	0.2	40	ms
$T_{VCCBRAM}$	Ramp time from GND to 95% of V_{CCBRAM} .	0.2	40	ms
$T_{MGTAVCC}$	Ramp time from GND to 95% of $V_{MGTAVCC}$.	0.2	40	ms
$T_{MGTAVTT}$	Ramp time from GND to 95% of $V_{MGTAVTT}$.	0.2	40	ms
$T_{MGTVCCAUX}$	Ramp time from GND to 95% of $V_{MGTVCCAUX}$.	0.2	40	ms
$T_{VCC_PSINTFP}$	Ramp time from GND to 95% of $V_{CC_PSINTFP}$.	0.2	40	ms
$T_{VCC_PSINTLP}$	Ramp time from GND to 95% of $V_{CC_PSINTLP}$.	0.2	40	ms
T_{VCC_PSAUX}	Ramp time from GND to 95% of V_{CC_PSAUX} .	0.2	40	ms
$T_{VCC_PSINTFP_DDR}$	Ramp time from GND to 95% of $V_{CC_PSINTFP_DDR}$.	0.2	40	ms
T_{VCC_PSADC}	Ramp time from GND to 95% of V_{CC_PSADC} .	0.2	40	ms
T_{VCC_PSPLL}	Ramp time from GND to 95% of V_{CC_PSPLL} .	0.2	40	ms
$T_{PS_MGTRAVCC}$	Ramp time from GND to 95% of $V_{CC_MGTRAVCC}$.	0.2	40	ms
$T_{PS_MGTRAVTT}$	Ramp time from GND to 95% of $V_{CC_MGTRAVTT}$.	0.2	40	ms

Table 26: Speed Grade Designations by Device (Cont'd)

Device	Speed Grade, Temperature Ranges, and V _{CCINT} Operating Voltages		
	Advance	Preliminary	Production
XCZU5EG	-3E (V _{CCINT} = 0.90V), -2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V), -2LE (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V), -1I (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V), -1LI (V _{CCINT} = 0.72V)		
XCZU5EV	-3E (V _{CCINT} = 0.90V), -2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V), -2LE (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V), -1I (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V), -1LI (V _{CCINT} = 0.72V)		
XCZU6CG	-2LE (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V) -1LI (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.72V)		-2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V) -1I (V _{CCINT} = 0.85V)
XCZU6EG	-3E (V _{CCINT} = 0.90V) -2LE (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V) -1LI (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.72V)		-2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V) -1I (V _{CCINT} = 0.85V)
XCZU7CG	-2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V), -2LE (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V), -1I (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V), -1LI (V _{CCINT} = 0.72V)		
XCZU7EG	-3E (V _{CCINT} = 0.90V), -2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V), -2LE (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V), -1I (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V), -1LI (V _{CCINT} = 0.72V)		
XCZU7EV	-3E (V _{CCINT} = 0.90V), -2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V), -2LE (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V), -1I (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V), -1LI (V _{CCINT} = 0.72V)		
XCZU9CG	-2LE (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V) -1LI (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.72V)		-2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V) -1I (V _{CCINT} = 0.85V)
XCZU9EG	-3E (V _{CCINT} = 0.90V) -2LE (V _{CCINT} = 0.85V) -2LE (V _{CCINT} = 0.72V) -1LI (V _{CCINT} = 0.85V) -1LI (V _{CCINT} = 0.72V)		-2E (V _{CCINT} = 0.85V) -2I (V _{CCINT} = 0.85V) -1E (V _{CCINT} = 0.85V) -1I (V _{CCINT} = 0.85V)

PS Configuration

Table 39: Processor Configuration Access Port Switching Characteristics

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
F_{PCAPCK}	Maximum processor configuration access port (PCAP) frequency.	200	200	200	150	150	MHz

Table 40: Boundary-Scan Port Switching Characteristics

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
F_{TCK}	JTAG clock maximum frequency.	25	25	25	15	15	MHz
T_{TAPTCK}/T_{TCKTAP}	TMS and TDI setup and hold.	4.0/2.0	4.0/2.0	4.0/2.0	5.0/2.0	5.0/2.0	ns, Min
T_{TCKTDO}	TCK falling edge to TDO output.	16.1	16.1	16.1	24	24	ns, Max

Notes:

- The test conditions are configured to the LVCMOS 3.3V I/O standard with a 12 mA drive strength.

Table 42: Linear Quad-SPI Interface⁽¹⁾

Symbol	Description	Load Conditions ⁽²⁾	Min	Max	Units
Quad-SPI device clock frequency operating at 100 MHz. Loopback enabled. LVCMOS 1.8V I/O standard.					
T _{DCQSPICLK5}	Quad-SPI clock duty cycle.	15 pF	45	55	%
		30 pF	45	55	%
T _{QSPISSCLK5}	Slave select asserted to next clock edge. ⁽³⁾	15 pF	5.0	–	ns
		30 pF	5.0	–	ns
T _{QSPISCLKSS5}	Clock edge to slave select deasserted.	15 pF	5.0	–	ns
		30 pF	5.0	–	ns
T _{QSPICKO5}	Clock to output delay, all outputs.	15 pF	3.2	7.4	ns
		30 pF	3.2	7.4	ns
T _{QSPIDCK5}	Setup time, all inputs.	15 pF	2.4	–	ns
		30 pF	2.4	–	ns
T _{QSPICKD5}	Hold time, all inputs.	15 pF	0.0	–	ns
		30 pF	0.0	–	ns
F _{QSPIREFCLK5}	Quad-SPI reference clock frequency.	15 pF	–	200	MHz
		30 pF	–	200	MHz
F _{QSPICLK5}	Quad-SPI device clock frequency.	15 pF	–	100	MHz
		30 pF	–	100	MHz

Notes:

1. The test conditions are configured for the linear Quad-SPI interface at 100 MHz with a 12 mA drive strength and fast slew rate.
2. 30 pF loads are for stacked modes.
3. T_{QSPISSCLK5} is only valid when two reference clock cycles are programmed between chip select and clock.

PS USB Interface

 Table 43: ULPI Interface⁽¹⁾

Symbol	Description	Min	Max	Units
T _{ULPIDCK}	Input setup to ULPI clock, all inputs.	4.5	–	ns
T _{ULPICKD}	Input hold to ULPI clock, all inputs.	0	–	ns
T _{ULPICKO}	ULPI clock to output valid, all outputs.	2.0	8.86	ns
F _{ULPICLK}	ULPI reference clock frequency.	–	60	MHz

Notes:

1. The test conditions are configured to the LVCMOS 3.3V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.

PS I2C Controller Interface

Table 47: I2C Interface⁽¹⁾

Symbol	Description	Min	Max	Units
I2C Fast-mode Interface				
$T_{I2CFCKL}$	SCL Low time.	1.3	–	μ s
$T_{I2CFCKH}$	SCL High time.	0.6	–	μ s
$T_{I2CFCKO}$	SDA clock to out delay.	–	900	ns
$T_{I2CFDCK}$	SDA input setup time.	100	–	ns
$F_{I2CFCLK}$	SCL clock frequency.	–	400	KHz
I2C Standard-mode Interface				
$T_{I2CSCKL}$	SCL Low time.	4.7	–	μ s
$T_{I2CSCKH}$	SCL High time.	4.0	–	μ s
$T_{I2CSCKO}$	SDA clock to out delay.	–	3450	ns
$T_{I2CSDCK}$	SDA input setup time.	250	–	ns
$F_{I2CSCLK}$	SCL clock frequency.	–	100	KHz

Notes:

1. The test conditions are configured to the LVCMOS 3.3V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.

Table 60: PS-GTR Transceiver Reference Clock Switching Characteristics

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
F _{GCLK}	Reference clock frequencies supported.	PCI Express	100 MHz			
		SATA	125 MHz or 150 MHz			
		USB 3.0	26 MHz, 52 MHz, or 100 MHz			
		DisplayPort	27 MHz, 108 MHz, or 135 MHz			
		SGMII	125 MHz			
T _{RCLK}	Reference clock rise time.	20% – 80%	–	200	–	ps
T _{FCLK}	Reference clock fall time.	80% – 20%	–	200	–	ps
T _{DCREF}	Reference clock duty cycle.	Transceiver PLL only.	40	–	60	%
		USB 3.0 with reference clock <40 MHz.	47.5	–	52.5	%

Table 67: USB 3.0 Protocol Characteristics (PS-GTR Transceivers)

Standard	Description	Line Rate (Mb/s)	Min	Max	Units
USB 3.0 Transmitter Jitter Generation					
USB 3.0	Total transmitter jitter.	5000	–	0.66	UI
USB 3.0 Receiver High Frequency Jitter Tolerance					
USB 3.0	Total receiver jitter tolerance.	5000	0.2	–	UI

Table 68: Serial-GMII Protocol Characteristics (PS-GTR Transceivers)

Standard	Description	Line Rate (Mb/s)	Min	Max	Units
Serial-GMII Transmitter Jitter Generation					
SGMII	Deterministic transmitter jitter.	1250	–	0.25	UI
Serial-GMII Receiver High Frequency Jitter Tolerance					
SGMII	Total receiver jitter tolerance.	1250	0.25	–	UI

PS System Monitor Specifications

Table 69: PS SYSMON Specifications

Parameter	Comments	Conditions	Min	Typ	Max	Units
$V_{CC_PSADC} = 1.8V \pm 3\%$, $T_j = -40^\circ C$ to $100^\circ C$, typical values at $T_j = 40^\circ C$						
ADC Accuracy ($T_j = -55^\circ C$ to $125^\circ C$) (1)						
Resolution			10	–	–	Bits
Sample rate			–	–	1	MS/s
RMS code noise	On-chip reference		–	1	–	LSBs
On-Chip Sensor Accuracy						
Temperature sensor error		$T_j = -55^\circ C$ to $110^\circ C$	–	–	± 3.5	$^\circ C$
		$T_j = 110^\circ C$ to $125^\circ C$	–	–	± 5	$^\circ C$
Supply sensor error(2)	Supply voltages less than or electrically connected to V_{CC_PSADC} .	$T_j = -40^\circ C$ to $125^\circ C$	–	–	± 1	%
	Supply voltages nominally at 1.8V but with the potential to go above V_{CC_PSADC} .	$T_j = -40^\circ C$ to $125^\circ C$	–	–	± 1.5	%
	Supply voltages nominally in the 2.0V to 3.3V range.	$T_j = -40^\circ C$ to $125^\circ C$	–	–	± 2.5	%

Notes:

- ADC offset errors are removed by enabling the ADC automatic offset calibration feature. The values are specified for when this feature is enabled.
- Supply sensor offset and gain errors are removed by enabling the automatic offset and gain calibration feature. The values are specified for when this feature is enabled.

Table 72: MIPI D-PHY Performance

Description	I/O Bank Type	Speed Grade and V _{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3 ⁽¹⁾	-2 ⁽¹⁾	-1	-2	-1	
MIPI D-PHY transmitter or receiver.	HP	1500	1500	1260	1260	1260	Mb/s

Notes:

- In the SBVA484 package, the data rate is 1260 Mb/s.

Table 73: LVDS Native-Mode 1000BASE-X Support⁽¹⁾

Description	I/O Bank Type	Speed Grade and V _{CCINT} Operating Voltages				
		0.90V	0.85V		0.72V	
		-3	-2	-1	-2	-1
1000BASE-X	HP	Yes				

Notes:

- 1000BASE-X support is based on the *IEEE Standard for CSMA/CD Access Method and Physical Layer Specifications* (IEEE Std 802.3-2008).

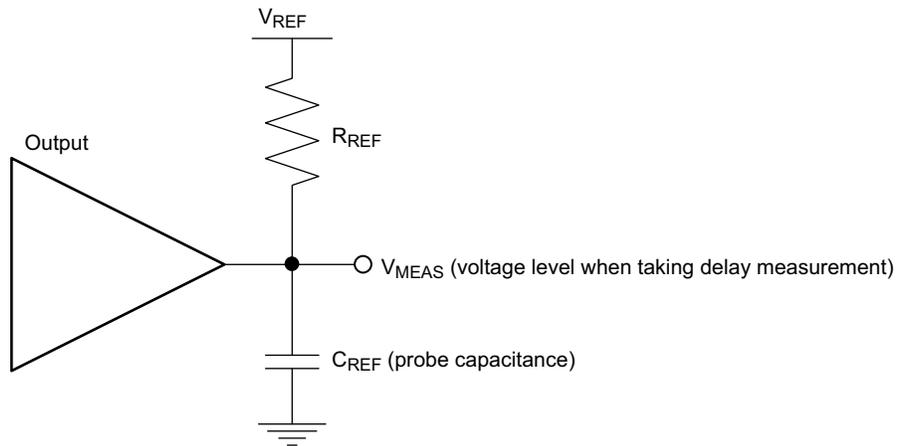
Table 74 provides the maximum data rates for applicable memory standards using the Zynq UltraScale+ MPSoC memory PHY. Refer to [Memory Interfaces](#) for the complete list of memory interface standards supported and detailed specifications. The final performance of the memory interface is determined through a complete design implemented in the Vivado Design Suite, following guidelines in the *UltraScale Architecture PCB Design Guide* ([UG583](#)), electrical analysis, and characterization of the system.

Table 74: Maximum Physical Interface (PHY) Rate for Memory Interfaces

Memory Standard	Package ⁽¹⁾	DRAM Type	Speed Grade and V _{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
DDR4	All FFV packages and FBVB900	Single rank component	2666	2666	2400	2400	2133	Mb/s
		1 rank DIMM ⁽²⁾⁽³⁾⁽⁴⁾	2400	2400	2133	2133	1866	Mb/s
		2 rank DIMM ⁽²⁾⁽⁵⁾	2133	2133	1866	1866	1600	Mb/s
		4 rank DIMM ⁽²⁾⁽⁶⁾	1600	1600	1333	1333	N/A	Mb/s
	SFVC784	Single rank component	2400	2400	2133	2133	1866	Mb/s
		1 rank DIMM ⁽²⁾⁽³⁾	2133	2133	1866	1866	1600	Mb/s
DDR3	All FFV packages and FBVB900	Single rank component	2133	2133	2133	2133	1866	Mb/s
		1 rank DIMM ⁽²⁾⁽³⁾	1866	1866	1866	1866	1600	Mb/s
		2 rank DIMM ⁽²⁾⁽⁵⁾	1600	1600	1600	1600	1333	Mb/s
		4 rank DIMM ⁽²⁾⁽⁶⁾	1066	1066	1066	1066	800	Mb/s
	SFVC784	Single rank component	1866	1866	1866	1866	1600	Mb/s
		1 rank DIMM ⁽²⁾⁽³⁾	1600	1600	1600	1600	1600	Mb/s
		2 rank DIMM ⁽²⁾⁽⁵⁾	1600	1600	1600	1600	1333	Mb/s
		4 rank DIMM ⁽²⁾⁽⁶⁾	1066	1066	1066	1066	800	Mb/s

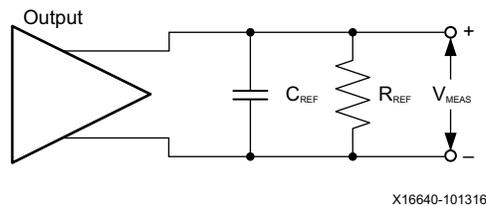
Output Delay Measurement Methodology

Output delays are measured with short output traces. Standard termination was used for all testing. The propagation delay of the trace is characterized separately and subtracted from the final measurement, and is therefore not included in the generalized test setups shown in [Figure 1](#) and [Figure 2](#).



X16654-101316

Figure 1: Single-Ended Test Setup



X16640-101316

Figure 2: Differential Test Setup

Parameters V_{REF} , R_{REF} , C_{REF} , and V_{MEAS} fully describe the test conditions for each I/O standard. The most accurate prediction of propagation delay in any given application can be obtained through IBIS simulation, using this method:

1. Simulate the output driver of choice into the generalized test setup using values from [Table 79](#).
2. Record the time to V_{MEAS} .
3. Simulate the output driver of choice into the actual PCB trace and load using the appropriate IBIS model or capacitance value to represent the load.
4. Record the time to V_{MEAS} .
5. Compare the results of [step 2](#) and [step 4](#). The increase or decrease in delay yields the actual propagation delay of the PCB trace.

Table 79: Output Delay Measurement Methodology

Description	I/O Standard Attribute	R _{REF} (Ω)	C _{REF} ⁽¹⁾ (pF)	V _{MEAS} (V)	V _{REF} (V)
LVC MOS, 1.2V	LVC MOS12	1M	0	0.6	0
LVC MOS, 1.5V	LVC MOS15	1M	0	0.75	0
LVC MOS, 1.8V	LVC MOS18	1M	0	0.9	0
LVC MOS, 2.5V	LVC MOS25	1M	0	1.25	0
LVC MOS, 3.3V	LVC MOS33	1M	0	1.65	0
LVTTL, 3.3V	LVTTL	1M	0	1.65	0
LVDCI, HSLVDCI, 1.5V	LVDCI_15, HSLVDCI_15	50	0	V _{REF}	0.75
LVDCI, HSLVDCI, 1.8V	LVDCI_15, HSLVDCI_18	50	0	V _{REF}	0.9
HSTL (high-speed transceiver logic), class I, 1.2V	HSTL_I_12	50	0	V _{REF}	0.6
HSTL, class I, 1.5V	HSTL_I	50	0	V _{REF}	0.75
HSTL, class I, 1.8V	HSTL_I_18	50	0	V _{REF}	0.9
HSUL (high-speed unterminated logic), 1.2V	HSUL_12	50	0	V _{REF}	0.6
SSTL12 (stub series terminated logic), 1.2V	SSTL12	50	0	V _{REF}	0.6
SSTL135 and SSTL135 class II, 1.35V	SSTL135, SSTL135_II	50	0	V _{REF}	0.675
SSTL15 and SSTL15 class II, 1.5V	SSTL15, SSTL15_II	50	0	V _{REF}	0.75
SSTL18, class I and class II, 1.8V	SSTL18_I, SSTL18_II	50	0	V _{REF}	0.9
POD10, 1.0V	POD10	50	0	V _{REF}	1.0
POD12, 1.2V	POD12	50	0	V _{REF}	1.2
DIFF_HSTL, class I, 1.2V	DIFF_HSTL_I_12	50	0	V _{REF}	0.6
DIFF_HSTL, class I, 1.5V	DIFF_HSTL_I	50	0	V _{REF}	0.75
DIFF_HSTL, class I, 1.8V	DIFF_HSTL_I_18	50	0	V _{REF}	0.9
DIFF_HSUL, 1.2V	DIFF_HSUL_12	50	0	V _{REF}	0.6
DIFF_SSTL12, 1.2V	DIFF_SSTL12	50	0	V _{REF}	0.6
DIFF_SSTL135 and DIFF_SSTL135 class II, 1.35V	DIFF_SSTL135, DIFF_SSTL135_II	50	0	V _{REF}	0.675
DIFF_SSTL15 and DIFF_SSTL15 class II, 1.5V	DIFF_SSTL15, DIFF_SSTL15_II	50	0	V _{REF}	0.75
DIFF_SSTL18, class I and II, 1.8V	DIFF_SSTL18_I, DIFF_SSTL18_II	50	0	V _{REF}	0.9
DIFF_POD10, 1.0V	DIFF_POD10	50	0	V _{REF}	1.0
DIFF_POD12, 1.2V	DIFF_POD12	50	0	V _{REF}	1.2
LVDS (low-voltage differential signaling), 1.8V	LVDS	100	0	0 ⁽²⁾	0
SUB_LVDS, 1.8V	SUB_LVDS	100	0	0 ⁽²⁾	0
MIPI D-PHY (high speed) 1.2V	MIPI_DPHY_DCI_HS	100	0	0 ⁽²⁾	0
MIPI D-PHY (low power) 1.2V	MIPI_DPHY_DCI_LP	1M	0	0.6	0

Notes:

1. C_{REF} is the capacitance of the probe, nominally 0 pF.
2. The value given is the differential output voltage.

UltraRAM Switching Characteristics

The *UltraScale Architecture and Product Overview* ([DS890](#)) lists the Zynq UltraScale+ MPSoC that include this memory.

Table 81: UltraRAM Switching Characteristics

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
Maximum Frequency							
F _{MAX}	UltraRAM maximum frequency with OREG_B = True.	650	600	575	500	481	MHz
F _{MAX_ECC}	UltraRAM maximum frequency with OREG_B = False and EN_ECC_RD_B = True.	450	400	386	325	315	MHz
F _{MAX_NORPIPELINE}	UltraRAM maximum frequency with OREG_B = False and EN_ECC_RD_B = False.	550	500	478	425	408	MHz
T _{PW} ⁽¹⁾	Minimum pulse width.	650	700	730	800	832	ps
T _{RSTPW}	Asynchronous reset minimum pulse width. One cycle required.	1 clock cycle					

Notes:

1. The MMCM and PLL DUTY_CYCLE attribute should be set to 50% to meet the pulse-width requirements at the higher frequencies.

Input/Output Delay Switching Characteristics

Table 82: Input/Output Delay Switching Characteristics

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
F _{REFCLK}	REFCLK frequency for IDELAYCTRL (component mode).	300 to 800					MHz
	REFCLK frequency for BITSLICE_CONTROL (native mode). ⁽¹⁾	300 to 2666.67	300 to 2666.67	300 to 2400	300 to 2400	300 to 2133	MHz
T _{MINPER_CLK}	Minimum period for IODELAY clock.	3.195	3.195	3.195	3.195	3.195	ns
T _{MINPER_RST}	Minimum reset pulse width.	52.00					ns
T _{IDELAY_RESOLUTION} / T _{ODELAY_RESOLUTION}	IDELAY/ODELAY chain resolution.	2.1 to 12					ps

Notes:

1. PLL settings could restrict the minimum allowable data rate. For example, when using a PLL with CLKOUTPHY_MODE = VCO_HALF, the minimum frequency is PLL_FVCOMIN/2.

Table 103: GTH Transceiver Transmitter Switching Characteristics

Symbol	Description	Condition	Min	Typ	Max	Units
F _{GTHTX}	Serial data rate range		0.500	–	F _{GTHMAX}	Gb/s
T _{RTX}	TX rise time	20%–80%	–	21	–	ps
T _{FTX}	TX fall time	80%–20%	–	21	–	ps
T _{LLSKEW}	TX lane-to-lane skew ⁽¹⁾		–	–	500.00	ps
T _{J16.375}	Total jitter ⁽²⁾⁽⁴⁾	16.375 Gb/s	–	–	0.28	UI
D _{J16.375}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J15.0}	Total jitter ⁽²⁾⁽⁴⁾	15.0 Gb/s	–	–	0.28	UI
D _{J15.0}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J14.1}	Total jitter ⁽²⁾⁽⁴⁾	14.1 Gb/s	–	–	0.28	UI
D _{J14.1}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J14.1}	Total jitter ⁽²⁾⁽⁴⁾	14.025 Gb/s	–	–	0.28	UI
D _{J14.1}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J13.1}	Total jitter ⁽²⁾⁽⁴⁾	13.1 Gb/s	–	–	0.28	UI
D _{J13.1}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J12.5_QPLL}	Total jitter ⁽²⁾⁽⁴⁾	12.5 Gb/s	–	–	0.28	UI
D _{J12.5_QPLL}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J12.5_CPLL}	Total jitter ⁽³⁾⁽⁴⁾	12.5 Gb/s	–	–	0.33	UI
D _{J12.5_CPLL}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.17	UI
T _{J11.3_QPLL}	Total jitter ⁽²⁾⁽⁴⁾	11.3 Gb/s	–	–	0.28	UI
D _{J11.3_QPLL}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J10.3125_QPLL}	Total jitter ⁽²⁾⁽⁴⁾	10.3125 Gb/s	–	–	0.28	UI
D _{J10.3125_QPLL}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J10.3125_CPLL}	Total jitter ⁽³⁾⁽⁴⁾	10.3125 Gb/s	–	–	0.33	UI
D _{J10.3125_CPLL}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.17	UI
T _{J9.953_QPLL}	Total jitter ⁽²⁾⁽⁴⁾	9.953 Gb/s	–	–	0.28	UI
D _{J9.953_QPLL}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J9.953_CPLL}	Total jitter ⁽³⁾⁽⁴⁾	9.953 Gb/s	–	–	0.33	UI
D _{J9.953_CPLL}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.17	UI
T _{J8.0}	Total jitter ⁽³⁾⁽⁴⁾	8.0 Gb/s	–	–	0.32	UI
D _{J8.0}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.17	UI
T _{J6.6}	Total jitter ⁽³⁾⁽⁴⁾	6.6 Gb/s	–	–	0.30	UI
D _{J6.6}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.15	UI
T _{J5.0}	Total jitter ⁽³⁾⁽⁴⁾	5.0 Gb/s	–	–	0.30	UI
D _{J5.0}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.15	UI
T _{J4.25}	Total jitter ⁽³⁾⁽⁴⁾	4.25 Gb/s	–	–	0.30	UI
D _{J4.25}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.15	UI
T _{J4.0}	Total jitter ⁽³⁾⁽⁴⁾	4.0 Gb/s	–	–	0.32	UI
D _{J4.0}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.16	UI
T _{J3.20}	Total jitter ⁽³⁾⁽⁴⁾	3.20 Gb/s ⁽⁵⁾	–	–	0.20	UI
D _{J3.20}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.10	UI

Table 115: GTY Transceiver Transmitter Switching Characteristics

Symbol	Description	Condition	Min	Typ	Max	Units
F _{GTYTX}	Serial data rate range		0.500	–	F _{GTYMAX}	Gb/s
T _{RTX}	TX rise time	20%–80%	–	21	–	ps
T _{FTX}	TX fall time	80%–20%	–	21	–	ps
T _{LLSKEW}	TX lane-to-lane skew ⁽¹⁾		–	–	500.00	ps
T _{J32.75}	Total jitter ⁽²⁾⁽⁴⁾	32.75 Gb/s	–	–	0.35	UI
D _{J32.75}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.19	UI
T _{J28.21}	Total jitter ⁽²⁾⁽⁴⁾	28.21 Gb/s	–	–	0.28	UI
D _{J28.21}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J16.375}	Total jitter ⁽²⁾⁽⁴⁾	16.375 Gb/s	–	–	0.28	UI
D _{J16.375}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J15.0}	Total jitter ⁽²⁾⁽⁴⁾	15.0 Gb/s	–	–	0.28	UI
D _{J15.0}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J14.1}	Total jitter ⁽²⁾⁽⁴⁾	14.1 Gb/s	–	–	0.28	UI
D _{J14.1}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J14.1}	Total jitter ⁽²⁾⁽⁴⁾	14.025 Gb/s	–	–	0.28	UI
D _{J14.1}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J13.1}	Total jitter ⁽²⁾⁽⁴⁾	13.1 Gb/s	–	–	0.28	UI
D _{J13.1}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J12.5_QPLL}	Total jitter ⁽²⁾⁽⁴⁾	12.5 Gb/s	–	–	0.28	UI
D _{J12.5_QPLL}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J12.5_CPLL}	Total jitter ⁽³⁾⁽⁴⁾	12.5 Gb/s	–	–	0.33	UI
D _{J12.5_CPLL}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.17	UI
T _{J11.3_QPLL}	Total jitter ⁽²⁾⁽⁴⁾	11.3 Gb/s	–	–	0.28	UI
D _{J11.3_QPLL}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J10.3125_QPLL}	Total jitter ⁽²⁾⁽⁴⁾	10.3125 Gb/s	–	–	0.28	UI
D _{J10.3125_QPLL}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J10.3125_CPLL}	Total jitter ⁽³⁾⁽⁴⁾	10.3125 Gb/s	–	–	0.33	UI
D _{J10.3125_CPLL}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.17	UI
T _{J9.953_QPLL}	Total jitter ⁽²⁾⁽⁴⁾	9.953 Gb/s	–	–	0.28	UI
D _{J9.953_QPLL}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J9.953_CPLL}	Total jitter ⁽³⁾⁽⁴⁾	9.953 Gb/s	–	–	0.33	UI
D _{J9.953_CPLL}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.17	UI
T _{J8.0}	Total jitter ⁽³⁾⁽⁴⁾	8.0 Gb/s	–	–	0.32	UI
D _{J8.0}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.17	UI
T _{J6.6}	Total jitter ⁽³⁾⁽⁴⁾	6.6 Gb/s	–	–	0.30	UI
D _{J6.6}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.15	UI
T _{J5.0}	Total jitter ⁽³⁾⁽⁴⁾	5.0 Gb/s	–	–	0.30	UI
D _{J5.0}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.15	UI
T _{J4.25}	Total jitter ⁽³⁾⁽⁴⁾	4.25 Gb/s	–	–	0.30	UI
D _{J4.25}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.15	UI

Integrated Interface Block for Interlaken

More information and documentation on solutions using the integrated interface block for Interlaken can be found at [UltraScale+ Interlaken](#). The *UltraScale Architecture and Product Overview (DS890)* lists how many blocks are in each Zynq UltraScale+ MPSoC. This section describes the following Interlaken configurations.

- 12 x 12.5 Gb/s protocol and lane logic mode ([Table 118](#)).
- 6 x 25.78125 Gb/s and 6 x 28.21 Gb/s protocol and lane logic mode ([Table 119](#)).
- 12 x 25.78125 Gb/s lane logic only mode ([Table 120](#)).

Zynq UltraScale+ MPSoCs in the SFVB784, FFVA676, and FFVA1156 packages are only supported using the 12 x 12.5 Gb/s Interlaken configuration. See [Table 109](#) for the F_{GTYMAX} description.

Table 118: Maximum Performance for Interlaken 12 x 12.5 Gb/s Protocol and Lane Logic Mode Designs

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages										Units
		0.90V		0.85V				0.72V				
		-3	-2	-1	-2	-1	-2	-1	-2	-1		
$F_{RX_SERDES_CLK}$	Receive serializer/deserializer clock	195.32		195.32				195.32				MHz
$F_{TX_SERDES_CLK}$	Transmit serializer/deserializer clock	195.32		195.32				195.32				MHz
F_{DRP_CLK}	Dynamic reconfiguration port clock	250.00		250.00				250.00				MHz
		Min ⁽¹⁾	Max	Min ⁽¹⁾	Max	Min ⁽¹⁾	Max	Min ⁽¹⁾	Max	Min ⁽¹⁾	Max	
F_{CORE_CLK}	Interlaken core clock	300.00	322.27	300.00	322.27	300.00	322.27	300.00	322.27	300.00	322.27	MHz
F_{LBUS_CLK}	Interlaken local bus clock	300.00	322.27	300.00	322.27	300.00	322.27	300.00	322.27	300.00	322.27	MHz

Notes:

1. These are the minimum clock frequencies at the maximum lane performance.

Integrated Interface Block for 100G Ethernet MAC and PCS

More information and documentation on solutions using the integrated 100 Gb/s Ethernet block can be found at [UltraScale+ Integrated 100G Ethernet MAC/PCS](#). The *UltraScale Architecture and Product Overview (DS890)* lists how many blocks are in each Zynq UltraScale+ MPSoC.

Table 121: Maximum Performance for 100G Ethernet Designs

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2 ⁽¹⁾	-1	-2	-1 ⁽²⁾	
F _{TX_CLK}	Transmit clock	390.625	390.625	322.223	322.223	322.223	MHz
F _{RX_CLK}	Receive clock	390.625	390.625	322.223	322.223	322.223	MHz
F _{RX_SERDES_CLK}	Receive serializer/deserializer clock	390.625	390.625	322.223	322.223	322.223	MHz
F _{DRP_CLK}	Dynamic reconfiguration port clock	250.00	250.00	250.00	250.00	250.00	MHz

Notes:

1. The maximum clock frequency of 390.625 MHz only applies to the CAUI-10 interface. The maximum clock frequency for the CAUI-4 interface is 322.223 MHz.
2. The CAUI-4 interface is not supported by -1L speed grade devices where V_{CCINT}=0.72V.

Integrated Interface Block for PCI Express Designs

More information and documentation on solutions for PCI Express designs can be found at [PCI Express](#). The *UltraScale Architecture and Product Overview (DS890)* lists the Zynq UltraScale+ MPSoCs that include this block.

Table 122: Maximum Performance for PCI Express Designs⁽¹⁾⁽²⁾

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
F _{PIPECLK}	Pipe clock maximum frequency.	250.00	250.00	250.00	250.00	250.00	MHz
F _{CORECLK}	Core clock maximum frequency.	500.00	500.00	500.00	250.00	250.00	MHz
F _{DRPCLK}	DRP clock maximum frequency.	250.00	250.00	250.00	250.00	250.00	MHz
F _{MCAPCLK}	MCAP clock maximum frequency.	125.00	125.00	125.00	125.00	125.00	MHz

Notes:

1. PCI Express Gen4 operation is supported for x1, x2, x4, and x8 widths.
2. PCI Express Gen4 operation is supported in -3E, -2E, and -2I speed grades.

PL SYSMON I2C/PMBus Interfaces

Table 125: PL SYSMON I2C Fast Mode Interface Switching Characteristics⁽¹⁾

Symbol	Description	Min	Max	Units
T_{SMFCKL}	SCL Low time	1.3	–	μ s
T_{SMFCKH}	SCL High time	0.6	–	μ s
T_{SMFCKO}	SDAO clock-to-out delay	–	900	ns
T_{SMFDCK}	SDAI setup time	100	–	ns
F_{SMFCLK}	SCL clock frequency	–	400	kHz

Notes:

1. The test conditions are configured to the LVCMOS 1.8V I/O standard.

Table 126: PL SYSMON I2C Standard Mode Interface Switching Characteristics⁽¹⁾

Symbol	Description	Min	Max	Units
T_{SMSCKL}	SCL Low time	4.7	–	μ s
T_{SMSCKH}	SCL High time	4.0	–	μ s
T_{SMSCKO}	SDAO clock-to-out delay	–	3450	ns
T_{SMSDCK}	SDAI setup time	250	–	ns
F_{SMSCLK}	SCL clock frequency	–	100	kHz

Notes:

1. The test conditions are configured to the LVCMOS 1.8V I/O standard.